

PHASE CONTROL THYRISTORS

Hockey Puk Version

Features

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case TO-200AC (B-PUK)

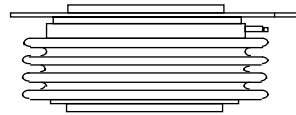
Typical Applications

- DC motor control
- Controlled DC power supplies
- AC controllers

Major Ratings and Characteristics

Parameters	ST650C..L	Units
$I_{T(AV)}$	790	A
@ T_{hs}	55	°C
$I_{T(RMS)}$	1557	A
@ T_{hs}	25	°C
I_{TSM}	@ 50Hz	10100 A
	@ 60Hz	10700 A
I^2t	@ 50Hz	510 KA ² s
	@ 60Hz	475 KA ² s
V_{DRM}/V_{RRM}	2000 to 2400	V
t_q typical	200	μs
T_J	- 40 to 125	°C

790A



case style TO-200AC (B-PUK)

ST650C..L Series

Bulletin I25203 rev. B 04/00

International
IRF Rectifier**ELECTRICAL SPECIFICATIONS****Voltage Ratings**

Type number	Voltage Code	V_{DRM}/V_{RRM} , max. repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J \text{ max}$ mA
ST650C..L	20	2000	2100	80
	22	2200	2300	
	24	2400	2500	

On-state Conduction

Parameter	ST650C..L	Units	Conditions
$I_{T(AV)}$ Max. average on-state current @ Heatsink temperature	790 (324)	A	180° conduction, half sine wave
	55 (85)	°C	double side (single side) cooled
$I_{T(RMS)}$ Max. RMS on-state current	1857	A	DC @ 25°C heatsink temperature double side cooled
I_{TSM} Max. peak, one-cycle non-repetitive surge current	10100		t = 10ms No voltage
	10700		t = 8.3ms reapplied
	8600		t = 10ms 100% V_{RRM}
	9150		t = 8.3ms reapplied
I^2t Maximum I^2t for fusing	510	KA ² s	t = 10ms No voltage
	475		t = 8.3ms reapplied
	370		t = 10ms 100% V_{RRM}
	347		t = 8.3ms reapplied
$I^2\sqrt{t}$ Maximum $I^2\sqrt{t}$ for fusing	5100	KA ² √s	t = 0.1 to 10ms, no voltage reapplied
$V_{T(TO)1}$ Low level value of threshold voltage	1.04	V	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J \text{ max.}$
$V_{T(TO)2}$ High level value of threshold voltage	1.13		$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ max.}$
r_{t1} Low level value of on-state slope resistance	0.61	mΩ	$(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)}), T_J = T_J \text{ max.}$
r_{t2} High level value of on-state slope resistance	0.35		$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ max.}$
V_{TM} Max. on-state voltage	2.07	V	$I_{pk} = 1700A, T_J = T_J \text{ max, } t_p = 10ms$ sine pulse
I_H Maximum holding current	600	mA	$T_J = 25^\circ C$, anode supply 12V resistive load
I_L Typical latching current	1000		

Switching

Parameter	ST650C..L	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	1000	A/ μ s	Gate drive 20V, 20 Ω , $t_r \leq 1\mu$ s $T_J = T_J$ max, anode voltage $\leq 80\% V_{DRM}$
t_d Typical delay time	1.0	μ s	Gate current 1A, $di_g/dt = 1A/\mu$ s $V_d = 0.67\% V_{DRM}$, $T_J = 25^\circ\text{C}$
t_q Typical turn-off time	200		$I_{TM} = 750A$, $T_J = T_J$ max, $di/dt = 60A/\mu$ s, $V_R = 50V$ $dv/dt = 20V/\mu$ s, Gate 0V 100 Ω , $t_p = 500\mu$ s

Blocking

Parameter	ST650C..L	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/ μ s	$T_J = T_J$ max. linear to 80% rated V_{DRM}
I_{DRM} I_{RRM} Max. peak reverse and off-state leakage current	80	mA	$T_J = T_J$ max, rated V_{DRM}/V_{RRM} applied

Triggering

Parameter		ST650C..L		Units	Conditions
P _{GM}	Maximum peak gate power	10.0		W	T _J = T _J max, t _p ≤ 5ms
P _{G(AV)}	Maximum average gate power	2.0			T _J = T _J max, f = 50Hz, d% = 50
I _{GM}	Max. peak positive gate current	3.0		A	T _J = T _J max, t _p ≤ 5ms
+V _{GM}	Maximum peak positive gate voltage	20		V	T _J = T _J max, t _p ≤ 5ms
-V _{GM}	Maximum peak negative gate voltage	5.0			
I _{GT}	DC gate current required to trigger	TYP.	MAX.	mA	T _J = - 40°C T _J = 25°C T _J = 125°C Max. required gate trigger/ current/ voltage are the lowest value which will trigger all units 12V anode-to-cathode applied
		200	-		
		100	200		
		50	-		
V _{GT}	DC gate voltage required to trigger	2.5	-	V	T _J = - 40°C T _J = 25°C T _J = 125°C
		1.8	3.0		
		1.1	-		
I _{GD}	DC gate current not to trigger	10		mA	Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V _{DRM} anode-to-cathode applied
V _{GD}	DC gate voltage not to trigger	0.25		V	

ST650C..L Series

Bulletin I25203 rev. B 04/00

International
IOR Rectifier

Thermal and Mechanical Specification

Parameter	ST650C..L	Units	Conditions
T_J Max. operating temperature range	-40 to 125	°C	
T_{stg} Max. storage temperature range	-40 to 150		
R_{thJ-hs} Max. thermal resistance, junction to heatsink	0.073 0.031	K/W	DC operation single side cooled DC operation double side cooled
R_{thC-hs} Max. thermal resistance, case to heatsink	0.011 0.006	K/W	DC operation single side cooled DC operation double side cooled
F Mounting force, $\pm 10\%$	14700 (1500)	N (Kg)	
wt Approximate weight	255	g	
Case style	TO - 200AC (B-PUK)		See Outline Table

ΔR_{thJ-hs} Conduction

(The following table shows the increment of thermal resistance R_{thJ-hs} when devices operate at different conduction angles than DC)

Conduction angle	Sinusoidal conduction		Rectangular conduction		Units	Conditions
	Single Side	Double Side	Single Side	Double Side		
180°	0.009	0.009	0.006	0.006	K/W	$T_J = T_J \text{ max.}$
120°	0.011	0.011	0.011	0.011		
90°	0.014	0.014	0.015	0.015		
60°	0.020	0.020	0.021	0.021		
30°	0.036	0.036	0.036	0.036		

Ordering Information Table

Device Code							
ST	65	0	C	24	L	1	
1	2	3	4	5	6	7	8
1	- Thyristor						
2	- Essential part number						
3	- 0 = Converter grade						
4	- C = Ceramic Puk						
5	- Voltage code: Code x 100 = V_{RRM} (See Voltage Rating Table)						
6	- L = Puk Case TO-200AC (B-PUK)						
7	- 0 = Eyelet terminals (Gate and Auxiliary Cathode Unsoldered Leads)						
	1 = Fast-on terminals (Gate and Auxiliary Cathode Unsoldered Leads)						
	2 = Eyelet terminals (Gate and Auxiliary Cathode Soldered Leads)						
	3 = Fast-on terminals (Gate and Auxiliary Cathode Soldered Leads)						
8	- Critical dv/dt: None = 500V/ μ sec (Standard selection)						
	L = 1000V/ μ sec (Special selection)						

Outline Table

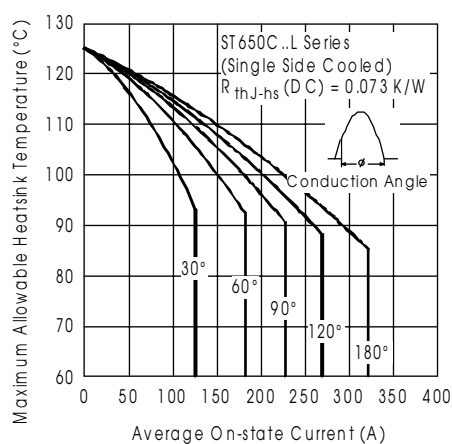
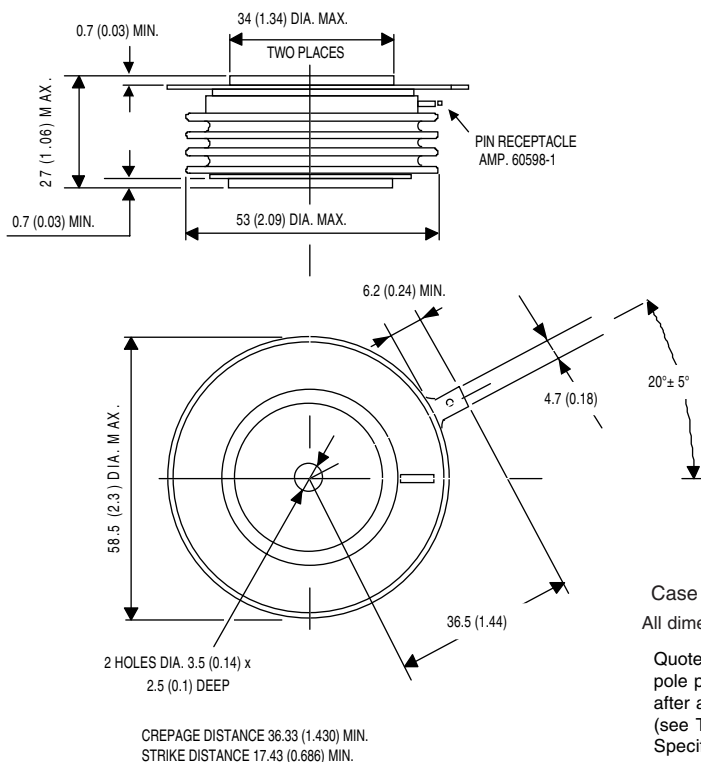


Fig. 1 - Current Ratings Characteristics

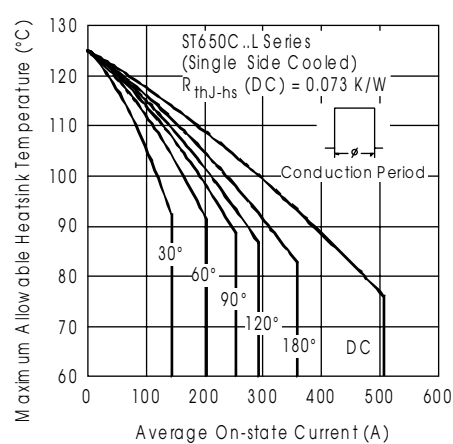


Fig. 2 - Current Ratings Characteristics

ST650C..L Series

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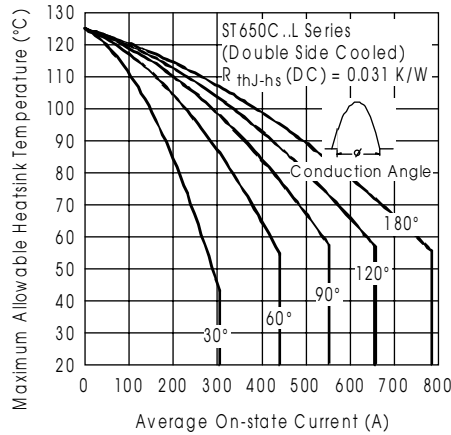


Fig. 3 - Current Ratings Characteristics

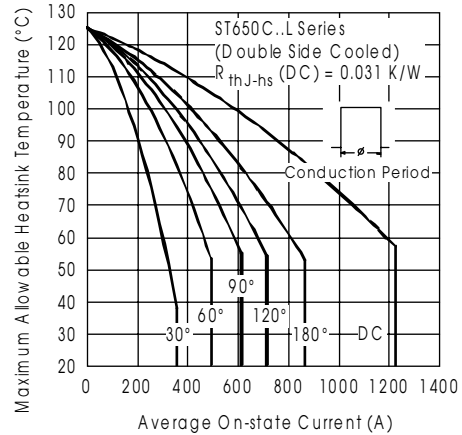


Fig. 4 - Current Ratings Characteristics

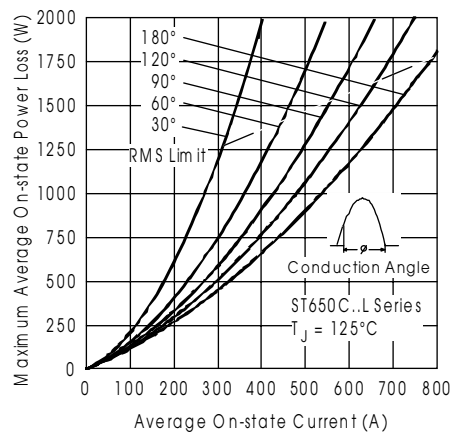


Fig. 5 - On-state Power Loss Characteristics

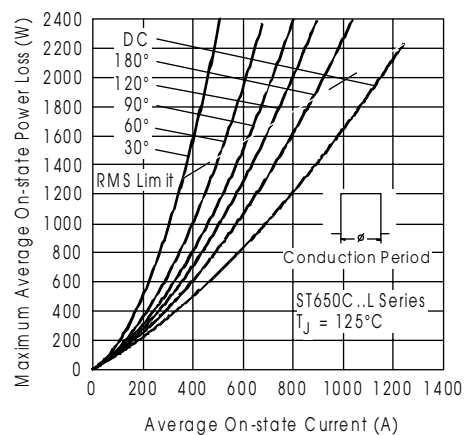


Fig. 6 - On-state Power Loss Characteristics

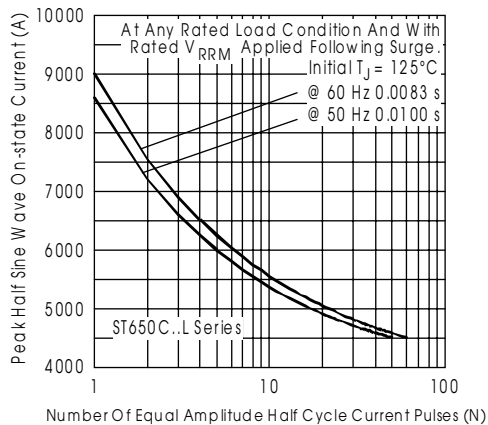


Fig. 7 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

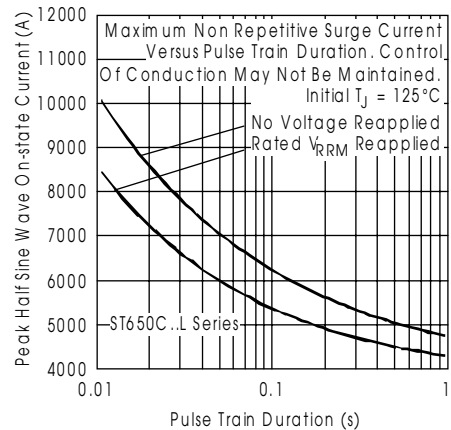


Fig. 8 - Maximum Non-Repetitive Surge Current
Single and Double Side Cooled

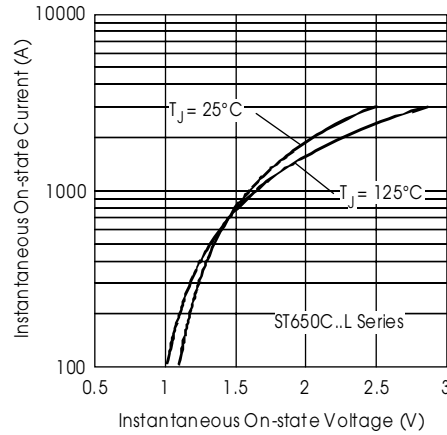


Fig. 9 - On-state Voltage Drop Characteristics

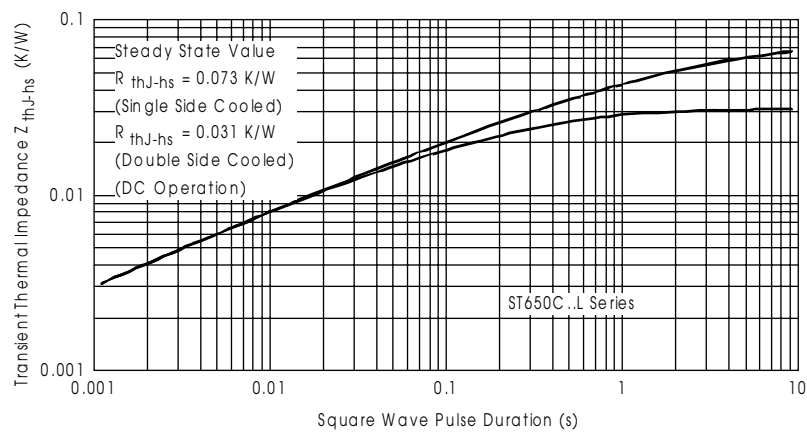


Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

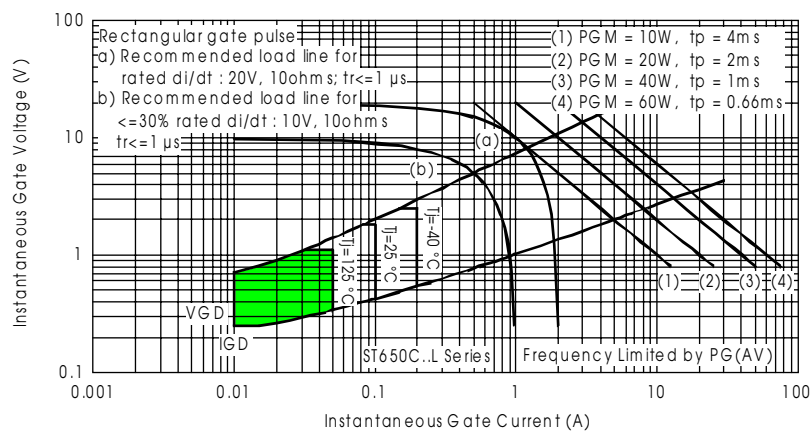


Fig. 11 - Gate Characteristics